

# 2SB1499, 2SB1499A

Silicon PNP epitaxial planar type

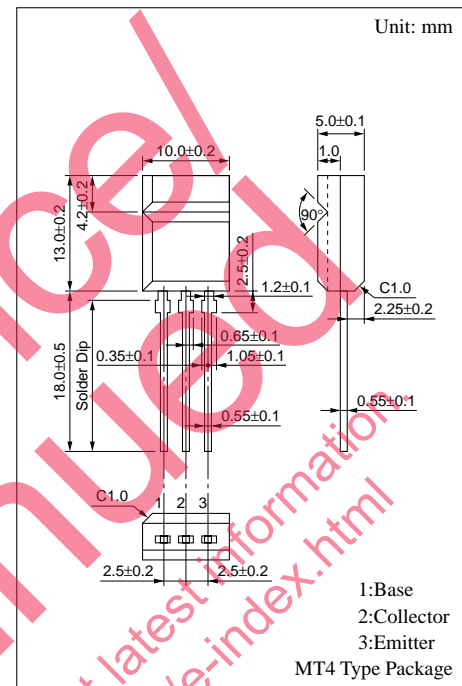
For low-frequency power amplification

## ■ Features

- High forward current transfer ratio  $h_{FE}$  which has satisfactory linearity
- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Allowing automatic insertion with radial tapping

## ■ Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-60	V
Collector to emitter voltage	$V_{CEO}$	-80	V
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-8	A
Collector current	$I_C$	-4	A
Collector power dissipation	$P_C$	15	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

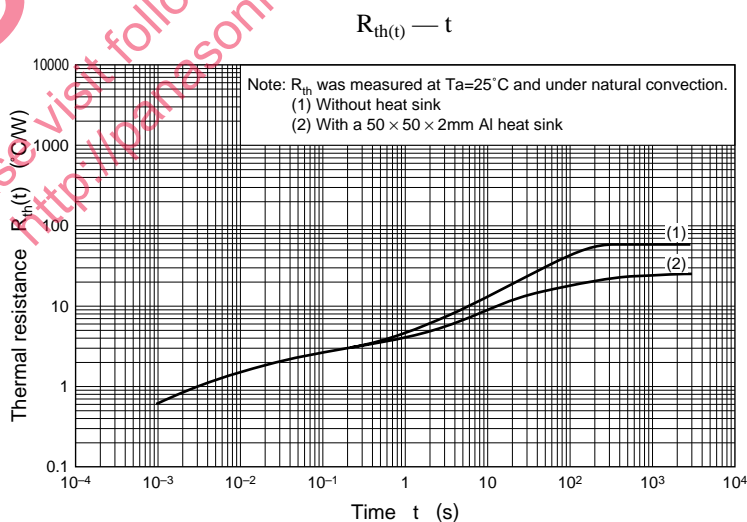
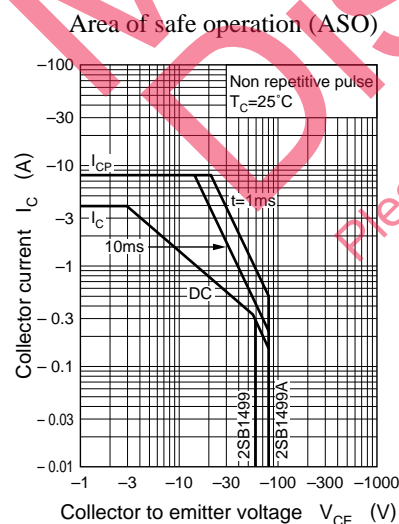
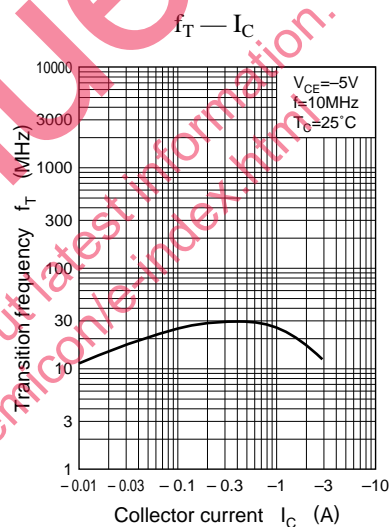
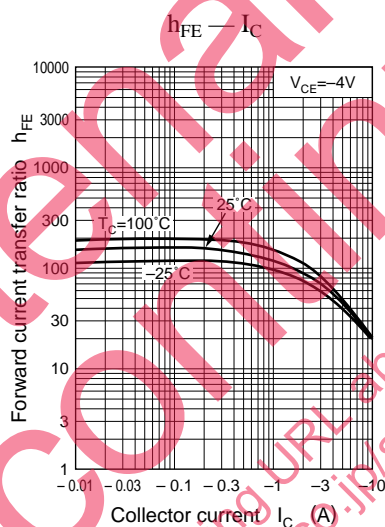
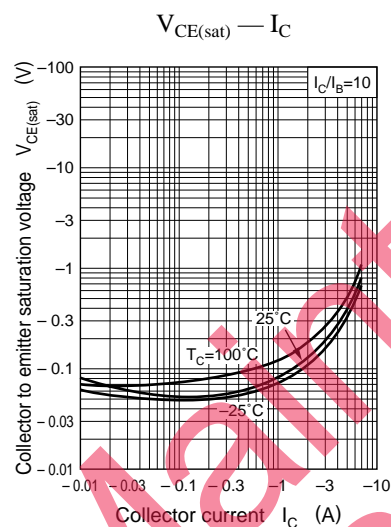
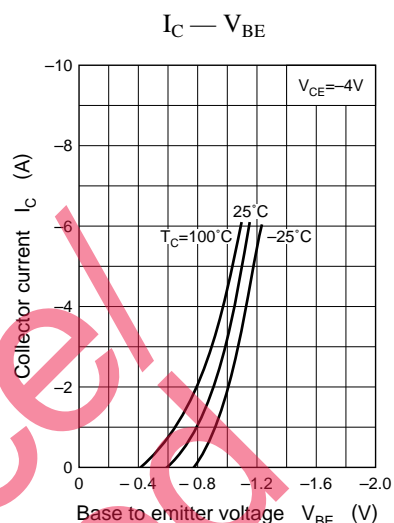
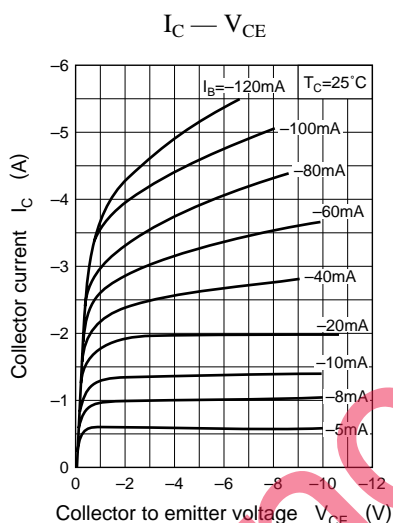
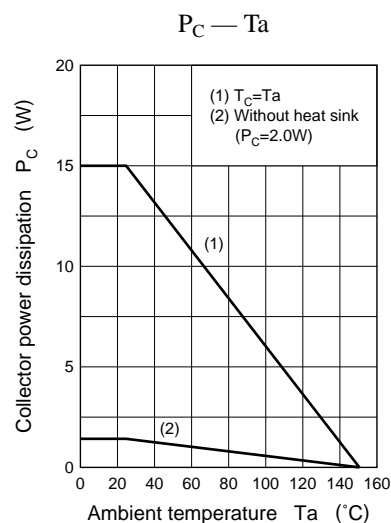


## ■ Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CES}$	$V_{CE} = -60\text{V}, V_{BE} = 0$			-400	$\mu\text{A}$
Collector cutoff current	$I_{CES}$	$V_{CE} = -80\text{V}, V_{BE} = 0$			-400	$\mu\text{A}$
Collector cutoff current	$I_{CEO}$	$V_{CE} = -30\text{V}, I_B = 0$			-700	$\mu\text{A}$
Collector cutoff current	$I_{CEO}$	$V_{CE} = -60\text{V}, I_B = 0$			-700	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-1	mA
Collector to emitter voltage	$V_{CEO}$	$I_C = -30\text{mA}, I_B = 0$	-60			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -30\text{mA}, I_B = 0$	-80			V
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = -4\text{V}, I_C = -1\text{A}$	70		250	
Forward current transfer ratio	$h_{FE2}$	$V_{CE} = -4\text{V}, I_C = -3\text{A}$	15			
Base to emitter voltage	$V_{BE}$	$V_{CE} = -4\text{V}, I_C = -3\text{A}$			-2	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4\text{A}, I_B = -0.4\text{A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -0.1\text{A}, f = 10\text{MHz}$		30		MHz
Turn-on time	$t_{on}$			0.2		$\mu\text{s}$
Storage time	$t_{stg}$	$I_C = -4\text{A}, I_{B1} = -0.4\text{A}, I_{B2} = 0.4\text{A}$		0.5		$\mu\text{s}$
Fall time	$t_f$			0.2		$\mu\text{s}$

\* $h_{FE1}$  Rank classification

Rank	Q	P
$h_{FE1}$	70 to 150	120 to 250



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